

Takahiko Endo

List of Publications by Year in descending order

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citing authors

#	ARTICLE	IF	CITATIONS
1	Formation of a Two-Dimensional Electronic System in Laterally Assembled WTe Nanowires. ACS Applied Nano Materials, 2022, 5, 6277-6284.	5.0	4
2	Nanowire-to-Nanoribbon Conversion in Transition-Metal Chalcogenides: Implications for One-Dimensional Electronics and Optoelectronics. ACS Applied Nano Materials, 2022, 5, 1775-1782.	5.0	7
3	Directional Exciton-Energy Transport in a Lateral Heteromonolayer of WSe_2 / MoSe_2 . ACS Nano, 2022, 16, 8205-8212.	14.6	20
4	Wafer-Scale Growth of One-Dimensional Transition-Metal Telluride Nanowires. Nano Letters, 2021, 21, 243-249.	9.1	18
5	Air-stable and efficient electron doping of monolayer MoS_2 by salt-crown ether treatment. Nanoscale, 2021, 13, 8784-8789.	5.6	12
6	Spatial Control of Dynamic p-n Junctions in Transition Metal Dichalcogenide Light-Emitting Devices. ACS Nano, 2021, 15, 12911-12921.	14.6	8
7	Control of Thermal Conductance across Vertically Stacked Two-Dimensional van der Waals Materials via Interfacial Engineering. ACS Nano, 2021, 15, 15902-15909.	14.6	11
8	ALD- ZrO_2 gate dielectric with suppressed interfacial oxidation for high performance MoS_2 top gate MOSFETs. Japanese Journal of Applied Physics, 2021, 60, SBBH03.	1.5	4
9	Versatile Post-Doping toward Two-Dimensional Semiconductors. ACS Nano, 2021, 15, 19225-19232.	14.6	14
10	Dynamical symmetry of strongly light-driven electronic system in crystalline solids. Communications Physics, 2020, 3, .	5.3	10
11	Synthesis and ambipolar transistor properties of tungsten diselenide nanotubes. Applied Physics Letters, 2020, 116, .	3.3	10
12	Momentum-forbidden dark excitons in hBN-encapsulated monolayer MoS_2 . Npj 2D Materials and Applications, 2019, 3, .	7.9	25
13	Chemically Tuned p-n and n-p type WSe_2 Monolayers with High Carrier Mobility for Advanced Electronics. Advanced Materials, 2019, 31, e1903613.	21.0	111
14	Chemical Doping: Chemically Tuned p-n and n-p type WSe_2 Monolayers with High Carrier Mobility for Advanced Electronics (Adv. Mater. 42/2019). Advanced Materials, 2019, 31, 1970301.	21.0	4
15	Monolayer MoS_2 growth at the Au/ SiO_2 interface. Nanoscale, 2019, 11, 19700-19704.	5.6	7
16	Restoring the intrinsic optical properties of CVD-grown MoS_2 monolayers and their heterostructures. Nanoscale, 2019, 11, 12798-12803.	5.6	37
17	Gas-Source CVD Growth of Atomic Layered WS_2 from WF_6 and H_2S Precursors with High Grain Size Uniformity. Scientific Reports, 2019, 9, 17678.	3.3	36
18	Comparative Study of High-k Dielectric on MoS_2 Deposited by Plasma Enhanced ALD. , 2019, , .		1